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TPS53355 High-Efficiency 30-A Synchronous Buck SWIFT™ Converter With Eco-mode[™]

Technical

Documents

Features 1

- 96% Maximum Efficiency
- Conversion Input Voltage Range: 1.5 V to 15 V
- VDD Input Voltage Range: 4.5 V to 25 V
- Output Voltage Range: 0.6 V to 5.5 V
- 5-V LDO Output
- Supports Single Rail Input
- Integrated Power MOSFETs with 30-A of Continuous Output Current
- Auto-Skip Eco-mode[™] for Light-Load Efficiency
- < 10-µA Shutdown Current
- D-CAP[™] Mode With Fast Transient Response
- Selectable Switching Frequency from 250 kHz to 1 MHz With External Resistor
- Selectable Auto-Skip or PWM-Only Operation
- Built-in 1% 0.6-V Reference.
- 0.7-ms, 1.4-ms, 2.8-ms and 5.6-ms Selectable Internal Voltage Servo Soft-Start
- Integrated Boost Switch
- Precharged Startup Capability
- Adjustable Overcurrent Limit with Thermal Compensation
- Overvoltage, Undervoltage, UVLO and **Overtemperature Protection**
- Supports All Ceramic Output Capacitors
- **Open-Drain Power Good Indication**
- Incorporates NexFET[™] Power Block Technology
- 22-Pin QFN Package With PowerPAD™
- For SWIFT[™] Power Products Documentation, see http://www.ti.com/swift
- Green (RoHS Compatible), is Optional

2 Applications

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- Workstations and Desktops
- **Telecommunications Infrastructure**

3 Description

TPS53355 is a D-CAP™ mode, 30-A synchronous switcher with integrated MOSFETs. It is designed for ease of use, low external component count, and space-conscious power systems.

This device features 5 m $\Omega/2.0$ m Ω integrated MOSFETs, accurate 1%, 0.6-V reference, and integrated boost switch. A sample of competitive features include: 1.5-V to 15-V wide conversion input voltage range, very low external component count, D-CAP[™] mode control for super fast transient, autoskip mode operation, internal soft-start control, selectable frequency, and no need for compensation.

The conversion input voltage ranges from 1.5 V to 15 V, the supply voltage range is from 4.5 V to 25 V, and the output voltage range is from 0.6 V to 5.5 V.

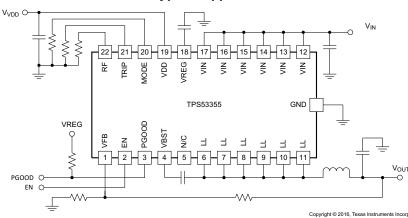
The device is available in 5-mm x 6-mm, 22-pin QFN package and is specified from -40°C to 85°C.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS53355	LSON-CLIP (22)	6.00 mm × 5.00 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Typical Application



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (February 2016) to Revision D

•	Added Feature: Green (RoHS Compatible), is Optional	. 1
•	Added the VQP package to the Thermal Infomation	. 6
•	From: a SC5026-1R0 inductor is used. To: a 744355182 inductor is used.	8
•	Changed Figure 32 and Figure 33	12
•	5-V LDO and VREG Start-Up, Changed the NOTE From: "The 5-V LDO is not controlled" To: "The 5-V LDO is controlled"	15
•	Changed 250 µs To ~550 µs in Figure 34	16

Changes from Revision B (January 2014) to Revision C

•	Changed the datasheet Title From: "TPS53355 High-Efficiency 30-A Synchronous Buck Converter With Eco-	
	mode™" To: "TPS53355 High-Efficiency 30-A Synchronous Buck SWIFT™ Converter With Eco-mode™" 1	
•	Added <i>Features</i> : "For SWIFT™ Power Products Documentation,"	

Changes from Revision A (September 2012) to Revision B

Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device

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Page

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Changes from Original (August 2011) to Revision A

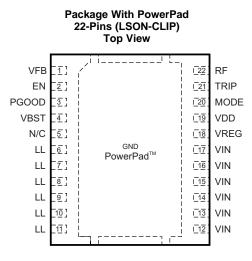
Page

_	
•	Changed conversion input voltage from "3 V" to "1.5 V" 1
•	Changed VIN input voltage range minimum from "3 V" to "1.5 V" 4
•	Changed typographical error in THERMAL INFORMATION table
•	Changed VIN (main supply) input voltage range minimum from "3 V' to "1.5 V" in Recommended Operating Conditions 5
•	Changed VIN pin power conversion input minimum voltage from "3 V" to "1.5 V" in ELECTRICAL CHARACTERISTICS table
•	Changed conversion input voltage range from "3 V" to "1.5" in Overview
•	Added note to the Functional Block Diagram
•	Changed "ripple injection capacitor" to "ripple injection resistor" in Layout Guidelines section

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5 Pin Configuration and Functions



(1) N/C = no connection

Pin Functions

PIN		I/O/P ⁽¹⁾	DESCRIPTION	
NAME	NO	I/U/F ···	DESCRIPTION	
EN	2	I	Enable pin. Typical turn-on threshold voltage is 1.2 V. Typical turn-off threshold is 0.95 V.	
GND		—	Ground and thermal pad of the device. Use proper number of vias to connect to ground plane.	
	6			
	7			
LL	8	8 B Output of converted power. Connect this pin to the output Inductor.	Output of converted power. Connect this pin to the output Inductor	
	9		ouput of converted power. Connect and pin to the output inductor.	
	10			
	11			
MODE	20	I	Soft-start and Skip/CCM selection. Connect a resistor to select soft-start time using Table 3. The soft-start time is detected and stored into internal register during start-up.	
N/C	5		No connect.	
PGOOD	3	0	Open drain power good flag. Provides 1-ms start-up delay after VFB falls in specified limits. When VFB goes out of the specified limits PGOOD goes low after a 2-µs delay.	
RF	22	I	Switching frequency selection. Connect a resistor to GND or VREG to select switching frequency using Table 1. The switching frequency is detected and stored during the startup.	
TRIP	21	I	OCL detection threshold setting pin. $I_{TRIP} = 10 \ \mu A$ at room temperature, 4700 ppm/°C current is sourced and set the OCL trip voltage as follows:	
			$V_{OCL} = V_{TRIP}/32$ ($V_{TRIP} \le 2.4 \text{ V}, V_{OCL} \le 75 \text{ mV}$)	
VBST	4	Р	Supply input for high-side FET gate driver (boost terminal). Connect capacitor from this pin to LL node. Internally connected to VREG via bootstrap MOSFET switch.	
VDD	19	Р	Controller power supply input. VDD input voltage range is from 4.5 V to 25 V.	
VFB	1	I	Output feedback input. Connect this pin to Vout through a resistor divider.	
	12			
	13			
VIN	14	Р	Conversion power input. VIN input voltage range is from 1.5 V to 15 V.	
VIIN	15	Г	Conversion power input. Vita input voltage range is norm 1.5 v to 15 v.	
	16			
	17			
VREG	18	Р	5-V low drop out (LDO) output. Supplies the internal analog circuitry and driver circuitry.	

(1) I=Input, O=Output, B=Bidirectional, P=Supply



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

			MIN	MAX	UNIT
	VIN (nain supply)	-0.3	25	
	VDD		-0.3	28	
Input voltage	VBST		-0.3	32	V
	VBST	(with respect to LL)	-0.3	7	
	EN, T	RIP, VFB, RF, MODE	-0.3	7	
		DC	-2	25	
Output weltere	LL Pulse < 20ns, E=5 μJ	Pulse < 20ns, E=5 μJ	-7	27	
Output voltage	PGO	DD, VREG	-0.3	7	V
	GND		-0.3	0.3	
Source/Sink current	VBST		50		mA
Operating free-air temp	erature,	Γ _Α	-40	85	
Junction temperature, T_J		-40	150	°C	
Lead temperature 1,6 n	ead temperature 1,6 mm (1/16 inch) from case for 10 seconds			300	
Storage temperature, T	prage temperature, T _{stg}		-55	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
	VIN (main supply)	1.5	15	
	VDD	4.5	25	
Input voltage range	VBST	4.5	28	V
	VBST (with respect to LL)	4.5	6.5	
	EN, TRIP, VFB, RF, MODE	-0.1	6.5	
	LL	-1	22	V
Output voltage range	PGOOD, VREG	-0.1	6.5	v
Junction temperature range, T_J	Junction temperature range, T _J		125	°C

TPS53355

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6.4 Thermal Infomation

		TPS5	TPS53355	
	THERMAL METRIC ⁽¹⁾	DQP	VQP	UNIT
		22 PINS	22 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	27.2	27.2	
θ_{JCtop}	Junction-to-case (top) thermal resistance	17.1	17.1	
θ_{JB}	Junction-to-board thermal resistance	5.9	5.9	°C/W
ΨJT	Junction-to-top characterization parameter	0.8	0.8	°C/VV
ΨJB	Junction-to-board characterization parameter	5.8	5.8	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	1.2	1.2	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

Over recommended free-air temperature range, V_{VDD} = 12 V (unless otherwise noted)

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY C	URRENT					
V _{VIN}	VIN pin power conversion input voltage		1.5		15	V
V _{VDD}	Supply input voltage		4.5		25.0	V
I _{VIN(leak)}	VIN pin leakage current	V _{EN} = 0 V			1	μA
I _{VDD}	VDD supply current	T_{A} = 25°C, No load, V_{EN} = 5 V, V_{VFB} = 0.630 V		420	590	μA
IVDDSDN	VDD shutdown current	$T_A = 25^{\circ}C$, No load, $V_{EN} = 0$ V			10	μA
INTERNAL	REFERENCE VOLTAGE					
V_{VFB}	VFB regulation voltage	CCM condition ⁽¹⁾		0.600		V
		$T_A = 25^{\circ}C$	0.597	0.600	0.603	
V_{VFB}	VFB regulation voltage	$0^{\circ}C \le T_{A} \le 85^{\circ}C$	0.5952	0.600	0.6048	V
		$-40^{\circ}C \le T_{A} \le 85^{\circ}C$	0.594	0.600	0.606	
I _{VFB}	VFB input current	$V_{VFB} = 0.630 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}$		0.01	0.20	μA
LDO OUTR	The					
V _{VREG}	LDO output voltage	$0 \text{ mA} \le I_{VREG} \le 30 \text{ mA}$	4.77	5.00	5.36	V
I _{VREG}	LDO output current ⁽¹⁾	Maximum current allowed from LDO			30	mA
V _{DO}	Low drop out voltage	V_{VDD} = 4.5 V, I_{VREG} = 30 mA			230	mV
BOOT STR	RAP SWITCH		-		i.	
V _{FBST}	Forward voltage	$V_{VREG-VBST}$, I_F = 10 mA, T_A = 25°C		0.1	0.2	V
I _{VBSTLK}	VBST leakage current	$V_{VBST} = 23 V, V_{SW} = 17 V, T_A = 25^{\circ}C$		0.01	1.50	μA
DUTY AND	FREQUENCY CONTROL					
t _{OFF(min)}	Minimum off time	$T_A = 25^{\circ}C$	150	260	400	ns
t _{ON(min)}	Minimum on time	$ \begin{array}{l} V_{\text{IN}} = 17 \; V, V_{\text{OUT}} = 0.6 \; V, \; R_{\text{RF}} = 39 \; \text{k}\Omega, \\ T_{\text{A}} = 25 \; ^{\circ}\text{C}^{(1)} \end{array} $		35		ns
SOFT STA	RT					
		$R_{MODE} = 39 \text{ k}\Omega$		0.7		
	Internal soft-start time from	R _{MODE} = 100 kΩ		1.4		
t_{SS} $V_{OUT} = 0 V to 95\% of V_{OUT}$	$V_{OUT} = 0 V$ to 95% of V_{OUT}	R _{MODE} = 200 kΩ	2.8			ms
		$R_{MODE} = 470 \text{ k}\Omega$		5.6		
INTERNAL	MOSFETS					
R _{DS(on)H}	High-side MOSFET on-resistance	$T_A = 25^{\circ}C$		5.0		mΩ
R _{DS(on)L}	Low-side MOSFET on-resistance	$T_A = 25^{\circ}C$		2.0		mΩ

(1) Ensured by design. Not production tested.



Electrical Characteristics (continued)

Over recommended free-air temperature range, V_{VDD}= 12 V (unless otherwise noted)

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
POWERGO	DOD					
		PG in from lower	92.5%	95.0%	98.5%	
V _{THPG}	PG threshold	PG in from higher	107.5%	110.0%	112.5%	
		PG hysteresis	2.5%	5.0%	7.5%	
R _{PG}	PG transistor on-resistance		15	30	55	Ω
t _{PGDEL}	PG delay	Delay for PG in	0.8	1	1.2	ms
	RESHOLD AND SETTING CONDITIONS	;				
V _{EN}	EN Voltage	Enable	1.8			V
	-	Disable			0.6	
I _{EN}	EN Input current	V _{EN} = 5 V			1.0	μA
		$R_{RF} = 0 \Omega$ to GND, $T_A = 25^{\circ}C^{(2)}$	200	250	300	-
		$R_{\rm RF}$ = 187 kΩ to GND, $T_{\rm A}$ = 25°C ⁽²⁾	250	300	350	
		$R_{RF} = 619 \text{ k}\Omega$, to GND, $T_A = 25^{\circ}C^{(2)}$	350	400	450	
		$R_{RF} = Open, T_A = 25^{\circ}C^{(2)}$	450	500	550	
f _{SW}	Switching frequency	R_{RF} = 866 k Ω to VREG, T_A = 25°C ⁽²⁾	580	650	720	kHz
		R_{RF} = 309 k Ω to VREG, T_A = 25°C ⁽²⁾	670	750	820	
		$R_{RF} = 124 \text{ k}\Omega$ to VREG, $T_A = 25^{\circ}C^{(2)}$	770	850	930	
		$R_{RF} = 0 \Omega$ to VREG, $T_A = 25^{\circ}C^{(2)}$	880	970	1070	
PROTECTI	ON: CURRENT SENSE	1				
I _{TRIP}	TRIP source current	V _{TRIP} = 1 V, T _A = 25°C	9.4	10.0	10.6	μA
TCITRIP	TRIP current temperature coefficient	On the basis of 25°C ⁽¹⁾		4700		ppm/°C
V _{TRIP}	Current limit threshold setting range	V _{TRIP-GND}	0.4		2.4	V
		$V_{TRIP} = 2.4 V$	68.5	75.0	81.5	
V _{OCL}	Current limit threshold	$V_{TRIP} = 0.4 V$	7.5	12.5	17.5	mV
		$V_{TRIP} = 2.4 V$	-315	-300	-285	
V _{OCLN}	Negative current limit threshold	$V_{\text{TRIP}} = 0.4 \text{ V}$	-58	-50	-42	mV
V _{AZCADJ}	Auto zero cross adjustable range	Positive	3	15		
		Negative		-15	-3	mV
PROTECTI	ON: UVP and OVP	-	-			
V _{OVP}	OVP trip threshold	OVP detect	115%	120%	125%	
t _{OVPDEL}	OVP propagation delay	VFB delay with 50-mV overdrive		1		μs
V _{UVP}	Output UVP trip threshold	UVP detect	65%	70%	75%	
tUVPDEL	Output UVP propagation delay		0.8	1.0	1.2	ms
t _{UVPEN}	Output UVP enable delay	From enable to UVP workable	1.8	2.6	3.2	ms
UVLO	-		I			
、 <i>,</i>		Wake up	4.00	4.20	4.33	
V _{UVVREG}	VREG UVLO threshold	Hysteresis		0.25		V
THERMAL	SHUTDOWN					
	Thermal shutdown threshold	Shutdown temperature ⁽¹⁾		145		°C
T _{SDN}		Hysteresis ⁽¹⁾		10		

(2) Not production tested. Test condition is V_{IN} = 12 V, V_{OUT} = 1.1 V, I_{OUT} = 10 A using application circuit shown in Figure 47.

TPS53355

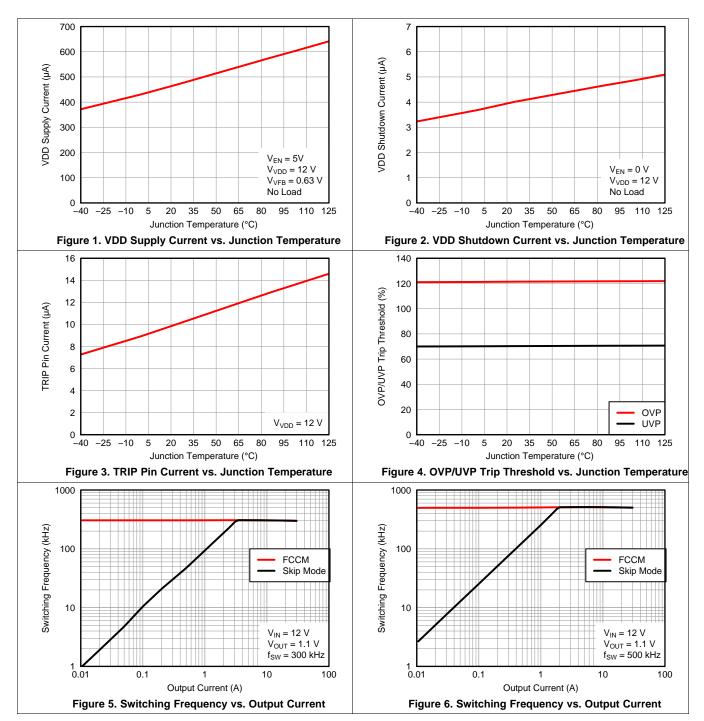
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6.6 Typical Characteristics

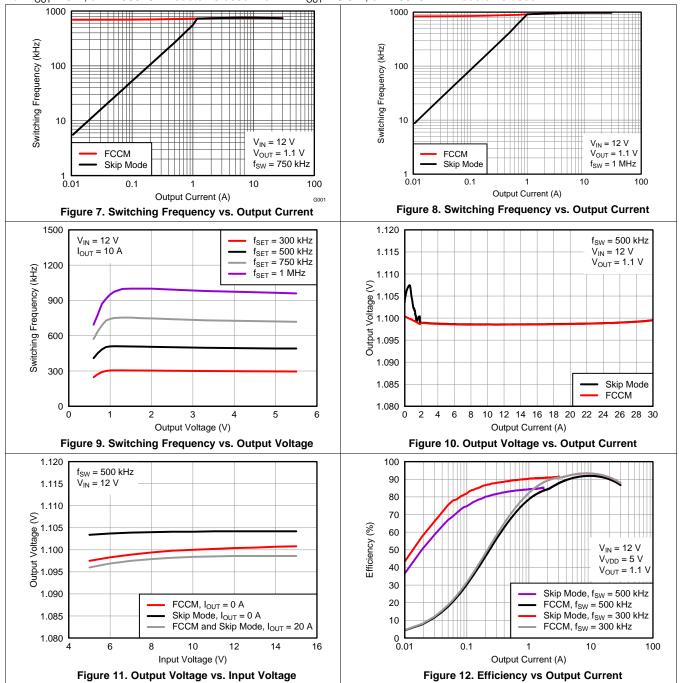
For V_{OUT} = 5 V, a 744355182 inductor is used. For 1 ≤ V_{OUT} ≤ 3.3 V, a PA0513.441 inductor is used.





Typical Characteristics (continued)

For $V_{OUT} = 5$ V, a 744355182 inductor is used. For $1 \le V_{OUT} \le 3.3$ V, a PA0513.441 inductor is used.

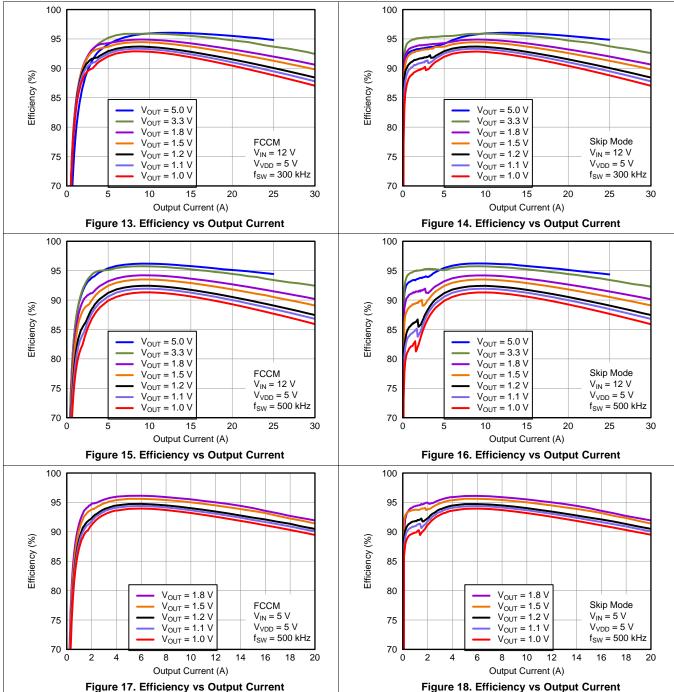


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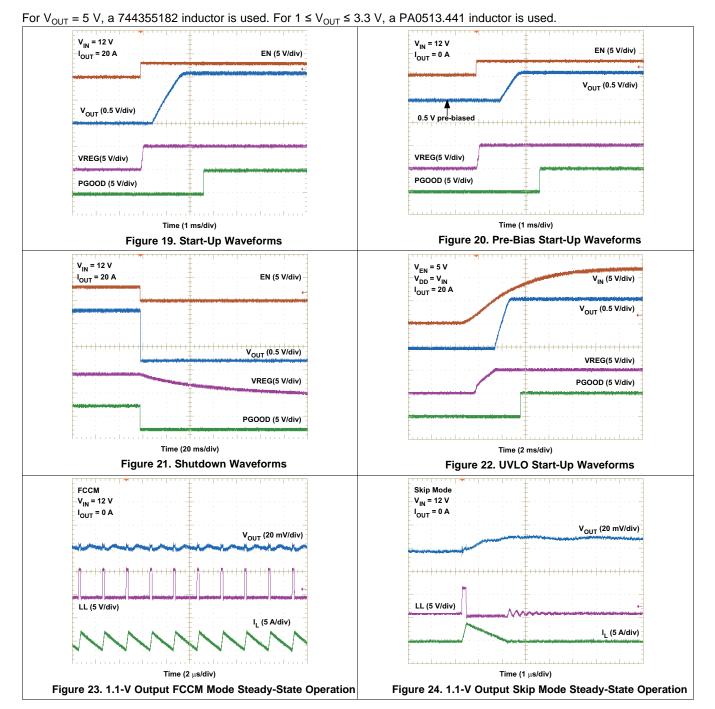
Typical Characteristics (continued)

For $V_{OUT} = 5$ V, a 744355182 inductor is used. For $1 \le V_{OUT} \le 3.3$ V, a PA0513.441 inductor is used.





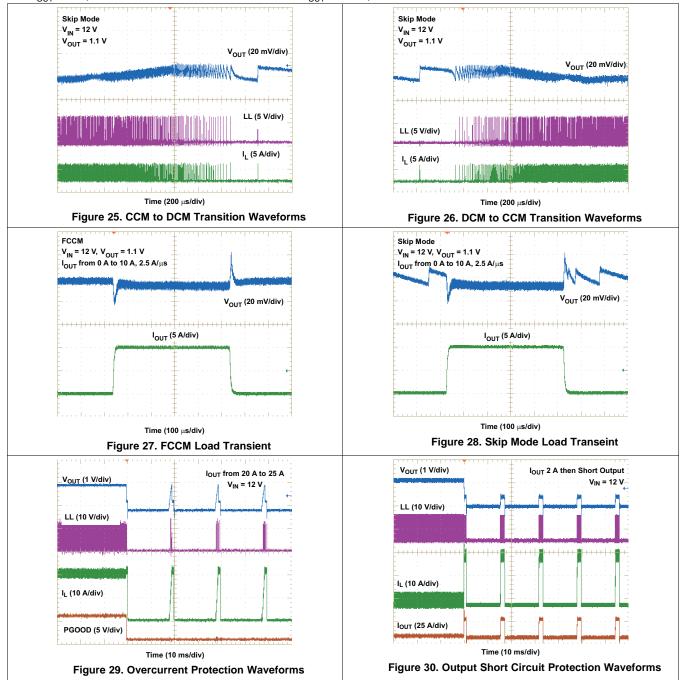
Typical Characteristics (continued)





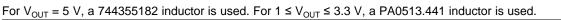
Typical Characteristics (continued)

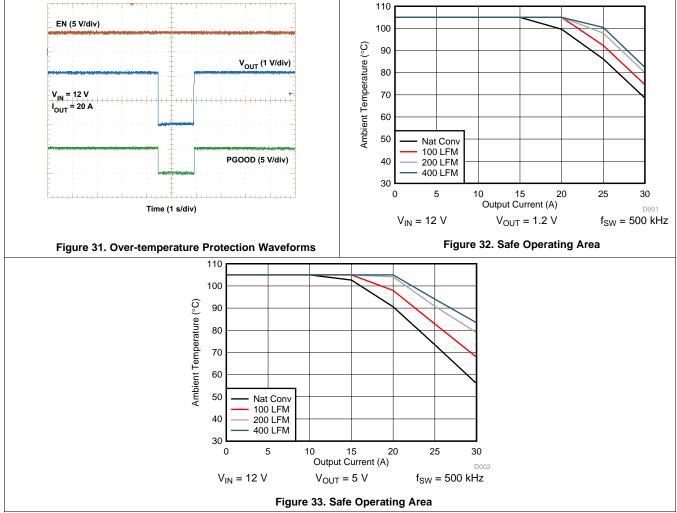
For $V_{OUT} = 5$ V, a 744355182 inductor is used. For $1 \le V_{OUT} \le 3.3$ V, a PA0513.441 inductor is used.





Typical Characteristics (continued)







7 Detailed Description

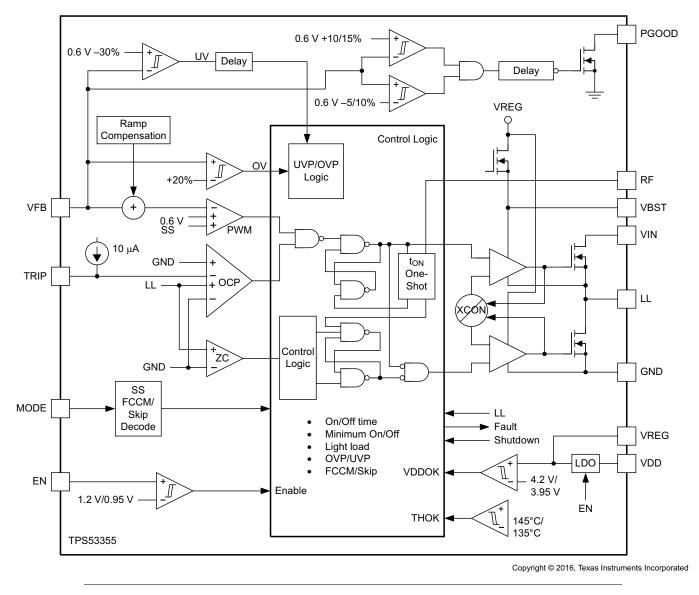
7.1 Overview

The TPS53355 is a high-efficiency, single channel, synchronous buck converter suitable for low output voltage point-of-load applications in computing and similar digital consumer applications. The device features proprietary D-CAP[™] mode control combined with an adaptive on-time architecture. This combination is ideal for building modern low duty ratio, ultra-fast load step response DC-DC converters. The output voltage ranges from 0.6 V to 5.5 V. The conversion input voltage range is from 1.5 V up to 15 V and the VDD bias voltage is from 4.5 V to 25 V. The D-CAP[™] mode uses the equivalent series resistance (ESR) of the output capacitor(s) to sense the device current. One advantage of this control scheme is that it does not require an external phase compensation network. This allows a simple design with a low external component count. Eight preset switching frequency values can be chosen using a resistor connected from the RF pin to ground or VREG. Adaptive on-time control tracks the preset switching frequency over a wide input and output voltage range while allowing the switching frequency to increase at the step-up of the load.

The TPS53355 has a MODE pin to select between auto-skip mode and forced continuous conduction mode (FCCM) for light load conditions. The MODE pin also sets the selectable soft-start time ranging from 0.7 ms to 5.6 ms as shown in Table 3.



7.2 Functional Block Diagram



NOTE

The thresholds in this block diagram are typical values. Refer to the *Electrical Characteristics* table for threshold limits.

7.3 Feature Description

7.3.1 5-V LDO and VREG Start-Up

TPS53355 provides an internal 5-V LDO function using input from VDD and output to VREG. When the VDD voltage rises above 2 V, the internal LDO is enabled and outputs voltage to the VREG pin. The VREG voltage provides the bias voltage for the internal analog circuitry and also provides the supply voltage for the gate drives.

NOTE The 5-V LDO is controlled by the EN pin. The LDO starts-up any time VDD rises to approximately 2 V. Figure 34

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Feature Description (continued)

7.3.2 Adaptive On-Time D-CAP Control and Frequency Selection

The TPS53355 does not have a dedicated oscillator to determine switching frequency. However, the device operates with pseudo-constant frequency by feed-forwarding the input and output voltages into the on-time one-shot timer. The adaptive on-time control adjusts the on-time to be inversely proportional to the input voltage and proportional to the output voltage ($t_{ON} \approx V_{OUT}/V_{IN}$).

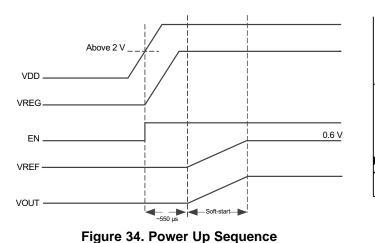
This makes the switching frequency fairly constant in steady state conditions over a wide input voltage range. The switching frequency is selectable from eight preset values by a resistor connected between the RF pin and GND or between the RF pin and the VREG pin as shown in Table 1. (Maintaining open resistance sets the switching frequency to 500 kHz.)

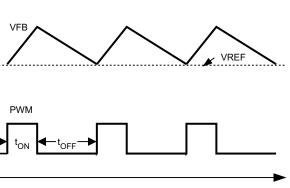
	5	1 2
	SISTOR (R _{RF}) INNECTIONS	SWITCHING FREQUENCY
VALUE (kΩ)	CONNECT TO	(f _{SW}) (kHz)
0	GND	250
187	GND	300
619	GND	400
OPEN	n/a	500
866	VREG	650
309	VREG	750
124	VREG	850
0	VREG	970

Table 1. Resistor and Switching Frequency

The off-time is modulated by a PWM comparator. The VFB node voltage (the mid-point of resistor divider) is compared to the internal 0.6-V reference voltage added with a ramp signal. When both signals match, the PWM comparator asserts a set signal to terminate the off time (turn off the low-side MOSFET and turn on high-side MOSFET). The set signal is valid if the inductor current level is below the OCP threshold, otherwise the off time is extended until the current level falls below the threshold.

Figure 35 and Figure 36 show two on-time control schemes.





UDG-10208

Figure 35. On-Time Control Without Ramp Compensation



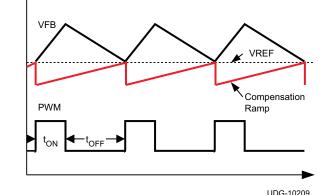


Figure 36. On-Time Control With Ramp Compensation

7.3.3 Ramp Signal

The TPS53355 adds a ramp signal to the 0.6-V reference in order to improve jitter performance. As described in the previous section, the feedback voltage is compared with the reference information to keep the output voltage in regulation. By adding a small ramp signal to the reference, the signal-to-noise ratio at the onset of a new switching cycle is improved. Therefore the operation becomes less jittery and more stable. The ramp signal is controlled to start with -7 mV at the beginning of an on-cycle and becomes 0 mV at the end of an off-cycle in steady state.

During skip mode operation, under discontinuous conduction mode (DCM), the switching frequency is lower than the nominal frequency and the off-time is longer than the off-time in CCM. Because of the longer off-time, the ramp signal extends after crossing 0 mV. However, it is clamped at 3 mV to minimize the DC offset.

7.3.4 Adaptive Zero Crossing

The TPS53355 has an adaptive zero crossing circuit which performs optimization of the zero inductor current detection at skip mode operation. This function pursues ideal low-side MOSFET turning off timing and compensates inherent offset voltage of the Z-C comparator and delay time of the Z-C detection circuit. It prevents SW-node swing-up caused by too late detection and minimizes diode conduction period caused by too early detection. As a result, better light load efficiency is delivered.

7.3.5 Power-Good

The TPS53355 has power-good output that indicates high when switcher output is within the target. The power-good function is activated after soft-start has finished. If the output voltage becomes within +10% and -5% of the target value, internal comparators detect power-good state and the power-good signal becomes high after a 1-ms internal delay. If the output voltage goes outside of +15% or -10% of the target value, the power-good signal becomes low after two microsecond (2- μ s) internal delay. The power-good output is an open drain output and must be pulled up externally.

The power-good MOSFET is powered through the VDD pin. V_{VDD} must be >1 V in order to have a valid power-good logic. It is recommended to pull PGOOD up to VREG (or a voltage divided from VREG) so that the power-good logic is still valid even without VDD supply.

7.3.6 Current Sense, Overcurrent and Short Circuit Protection

TPS53355 has cycle-by-cycle overcurrent limiting control. The inductor current is monitored during the *OFF* state and the controller maintains the *OFF* state during the period in that the inductor current is larger than the overcurrent trip level. In order to provide both good accuracy and cost effective solution, TPS53355 supports temperature compensated MOSFET $R_{DS(on)}$ sensing. The TRIP pin should be connected to GND through the trip voltage setting resistor, R_{TRIP} . The TRIP terminal sources current (I_{TRIP}) which is 10 μ A typically at room temperature, and the trip level is set to the OCL trip voltage V_{TRIP} as shown in Equation 1.

 $V_{\text{TRIP}}(mV) = R_{\text{TRIP}}(k\Omega) \times I_{\text{TRIP}}(\mu A)$

(1)

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The inductor current is monitored by the LL pin. The GND pin is used as the positive current sensing node and the LL pin is used as the negative current sense node. The trip current, I_{TRIP} has 4700ppm/°C temperature slope to compensate the temperature dependency of the $R_{DS(on)}$.

As the comparison is made during the *OFF* state, V_{TRIP} sets the valley level of the inductor current. Thus, the load current at the overcurrent threshold, I_{OCP} , can be calculated as shown in Equation 2.

$$I_{OCP} = \frac{V_{TRIP}}{\left(32 \times R_{DS(on)}\right)} + \frac{I_{IND(ripple)}}{2} = \frac{V_{TRIP}}{\left(32 \times R_{DS(on)}\right)} + \frac{1}{2 \times L \times f_{SW}} \times \frac{\left(V_{IN} - V_{OUT}\right) \times V_{OUT}}{V_{IN}}$$
(2)

In an overcurrent or short circuit condition, the current to the load exceeds the current to the output capacitor thus the output voltage tends to decrease. Eventually, it crosses the undervoltage protection threshold and shuts down. After a hiccup delay (16 ms with 0.7 ms sort-start), the controller restarts. If the overcurrent condition remains, the procedure is repeated and the device enters hiccup mode.

Hiccup time calculation:

 $t_{HIC(wait)} = (2^{n} + 257) \times 4 \ \mu s$

where

• n = 8, 9, 10, or 11 depending on soft start time selection $t_{HIC(dlv)} = 7 \times (2^n + 257) \times 4 \ \mu s$

Table 2. Hiccup Delay

SELECTED SOFT-START TIME (t _{SS}) (ms)	n	HICCUP WAIT TIME (t _{HIC(wait)}) (ms)	HICCUP DELAY TIME (t _{HIC(dly)}) (ms)
0.7	8	2.052	14.364
1.4	9	3.076	21.532
2.8	10	5.124	35.868
5.6	11	9.220	64.540

7.3.7 Overvoltage and Undervoltage Protection

TPS53355 monitors a resistor divided feedback voltage to detect over and under voltage. When the feedback voltage becomes lower than 70% of the target voltage, the UVP comparator output goes high and an internal UVP delay counter begins counting. After 1ms, TPS53355 latches OFF both high-side and low-side MOSFETs drivers. The controller restarts after a hiccup delay (16 ms with 0.7 ms soft-start). This function is enabled 1.5-ms after the soft-start is completed.

When the feedback voltage becomes higher than 120% of the target voltage, the OVP comparator output goes high and the circuit latches OFF the high-side MOSFET driver and latches ON the low-side MOSFET driver. The output voltage decreases. If the output voltage reaches UV threshold, then both high-side MOSFET and low-side MOSFET driver will be OFF and the device restarts after a hiccup delay. If the OV condition remains, both high-side MOSFET and low-side MOSFET driver remains OFF until the OV condition is removed.

7.3.8 UVLO Protection

The TPS53355 uses VREG undervoltage lockout protection (UVLO). When the VREG voltage is lower than 3.95 V, the device shuts off. When the VREG voltage is higher than 4.2 V, the device restarts. This is a non-latch protection.

7.3.9 Thermal Shutdown

TPS53355 monitors the temperature of itself. If the temperature exceeds the threshold value (typically 145°C), TPS53355 is shut off. When the temperature falls about 10°C below the threshold value, the device will turn back on. This is a non-latch protection.

(3)

(4)

7.4 Device Functional Modes

7.4.1 Enable, Soft Start, and Mode Selection

When the EN pin voltage rises above the enable threshold voltage (typically 1.2 V), the controller enters its startup sequence. The internal LDO regulator starts immediately and regulates to 5 V at the VREG pin. The controller then uses the first 250 μ s to calibrate the switching frequency setting resistance attached to the RF pin and stores the switching frequency code in internal registers. During this period, the MODE pin also senses the resistance attached to this pin and determines the soft-start time. Switching is inhibited during this phase. In the second phase, an internal DAC starts ramping up the reference voltage from 0 V to 0.6 V. Depending on the MODE pin setting, the ramping up time varies from 0.7 ms to 5.6 ms. Smooth and constant ramp-up of the output voltage is maintained during start-up regardless of load current.

MODE SELECTION	ACTION	SOFT-START TIME (ms)	R _{MODE} (kΩ)
		0.7	39
Auto Chin	Pull down to GND	1.4	100
Auto Skip	Pull down to GND	2.8	200
		5.6	475
		0.7	39
Forced CCM ⁽¹⁾		1.4	100
Forced CCM(*)	Connect to PGOOD	2.8	200
		5.6	475

Table 3. Soft-Start and MODE Settings

(1) Device enters FCCM after the PGOOD pin goes high when MODE is connected to PGOOD through the resistor R_{MODE} .

After soft-start begins, the MODE pin becomes the input of an internal comparator which determines auto skip or FCCM mode operation. If MODE voltage is higher than 1.3 V, the converter enters into FCCM mode. Otherwise it will be in auto skip mode at light load condition. Typically, when FCCM mode is selected, the MODE pin is connected to PGOOD through the R_{MODE} resistor, so that before PGOOD goes high the converter remains in auto skip mode.

7.4.2 Auto-Skip Eco-mode[™] Light Load Operation

While the MODE pin is pulled low via R_{MODE} , TPS53355 automatically reduces the switching frequency at light load conditions to maintain high efficiency. Detailed operation is described as follows. As the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to the point that its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The synchronous MOSFET is turned off when this zero inductor current is detected. As the load current further decreases, the converter runs into discontinuous conduction mode (DCM). The on-time is kept almost the same as it was in the continuous conduction mode so that it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. The transition point to the light-load operation $I_{OUT(LL)}$ (i.e., the threshold between continuous and discontinuous conduction mode) can be calculated as shown in Equation 5.

$$I_{OUT(LL)} = \frac{1}{2 \times L \times f_{SW}} \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}}$$

where

• f_{SW} is the PWM switching frequency

(5)

Switching frequency versus output current in the light load condition is a function of L, V_{IN} and V_{OUT} , but it decreases almost proportionally to the output current from the $I_{OUT(LL)}$ given in Equation 5. For example, it is 60 kHz at $I_{OUT(LL)}/5$ if the frequency setting is 300 kHz.

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7.4.3 Forced Continuous Conduction Mode

When the MODE pin is tied to PGOOD through a resistor, the controller keeps continuous conduction mode (CCM) in light load condition. In this mode, switching frequency is kept almost constant over the entire load range which is suitable for applications that need tight control of the switching frequency at a cost of lower efficiency.



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPS53355 is a high-efficiency, single channel, synchronous buck converter suitable for low output voltage point-of-load applications in computing and similar digital consumer applications. The device features proprietary D-CAP mode control combined with an adaptive on-time architecture. This combination is ideal for building modern low duty ratio, ultra-fast load step response DC-DC converters. The output voltage ranges from 0.6 V to 5.5 V. The conversion input voltage range is from 1.5 V up to 15 V and the VDD bias voltage is from 4.5 V to 25 V. The D-CAP mode uses the equivalent series resistance (ESR) of the output capacitor(s) to sense the device current. One advantage of this control scheme is that it does not require an external phase compensation network. This allows a simple design with a low external component count. Eight preset switching frequency values can be chosen using a resistor connected from the RF pin to ground or VREG. Adaptive on-time control tracks the preset switching frequency over a wide input and output voltage range while allowing the switching frequency to increase at the step-up of the load.

8.1.1 Small Signal Model

From small-signal loop analysis, a buck converter using D-CAP[™] mode can be simplified as shown in Figure 37.

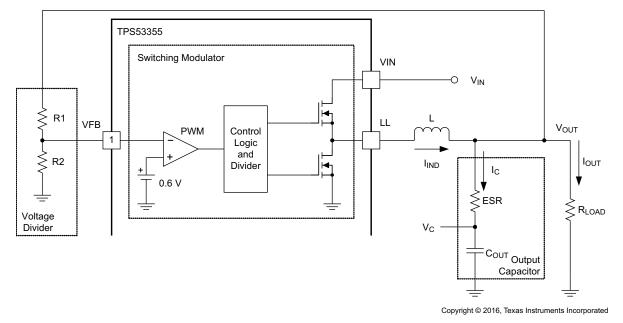


Figure 37. Simplified Modulator Model

The output voltage is compared with the internal reference voltage (ramp signal is ignored here for simplicity). The PWM comparator determines the timing to turn on the high-side MOSFET. The gain and speed of the comparator can be assumed high enough to keep the voltage at the beginning of each on cycle substantially constant.

$$H(s) = \frac{I}{s \times ESR \times C_{OUT}}$$

(6)

For loop stability, the 0-dB frequency, f_0 , defined below need to be lower than 1/4 of the switching frequency.

(7)

INSTRUMENTS

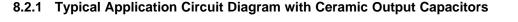
Texas

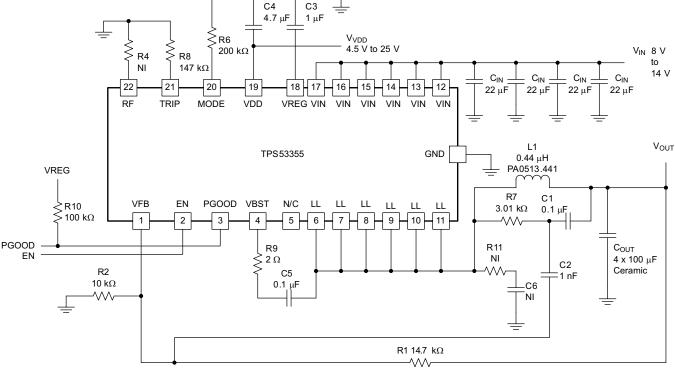
Application Information (continued)

$$f_0 = \frac{1}{2\pi \times \text{ESR} \times C_{OUT}} \le \frac{f_{SW}}{4}$$

According to the equation above, the loop stability of D-CAPTM mode modulator is mainly determined by the capacitor's chemistry. For example, specialty polymer capacitors (SP-CAP) have an output capacitance in the order of several 100 μ F and ESR in range of 10 m Ω . These makes f_0 on the order of 100 kHz or less, creating a stable loop. However, ceramic capacitors have an f_0 at more than 700 kHz, and need special care when used with this modulator. An application circuit for ceramic capacitor is described in *External Component Selection Using All Ceramic Output Capacitors*.

8.2 Typical Applications





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Figure 38. Typical Application Circuit Diagram with Ceramic Output Capacitors Schematic



Typical Applications (continued)

8.2.1.1 Design Requirements

	PARAMETER	TEST CONDITION	MIN	ТҮР	MAX	UNIT
INPUT CH	IARACTERISTICS					
V _{IN}	Voltage range		8	12	14	V
	Maximum input current	V _{IN} = 8 V, I _{OUT} = 30 A		6.3		А
I _{MAX}	No load input current	$V_{IN} = 14 \text{ V}, I_{OUT} = 0 \text{ A}$ with auto-skip mode		1		mA
OUTPUT	CHARACTERISTICS					
	Output voltage			1.5		
V _{OUT}		Line regulation, 8 V \leq V _{IN} \leq 15 V		0.1%		
Output voltage regulation	Load regulation, V_{IN} = 12 V, 0 A ≤ I_{OUT} ≤ 30 A with FCCM		0.2%			
V _{RIPPLE}	Output voltage ripple	$V_{IN} = 12 \text{ V}, I_{OUT} = 30 \text{ A with FCCM}$		20		mV _{PP}
I _{LOAD}	Output load current		0		30	А
I _{OCP}	Output overcurrent threshold			34		А
t _{SS}	Soft-start time			1.4		ms
SYSTEMS	S CHARACTERISTICS					
f _{SW}	Switching frequency			500		kHz
	Peak efficiency	V _{IN} = 12 V, V _{OUT} = 1.1 V, I _{OUT} = 10 A		91.87%		
η	Full load efficiency	V _{IN} = 12 V, V _{OUT} = 1.1 V, I _{OUT} = 30 A		89.46%		
T _A	Operating temperature			25		°C

Table 4. Design Parameters

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 External Component Selection

The external components selection is a simple process when using organic semiconductors or special polymer output capacitors.

1. Select operation mode and soft-start time

Select operation mode and soft-start time using Table 3.

2. Select switching frequency

Select the switching frequency from 250 kHz to 1 MHz using Table 1.

3. Choose the inductor

The inductance value should be determined to give the ripple current of approximately 1/4 to 1/2 of maximum output current. Larger ripple current increases output ripple voltage and improves signal-to-noise ratio and helps ensure stable operation, but increases inductor core loss. Using 1/3 ripple current to maximum output current ratio, the inductance can be determined by Equation 8.

$$L = \frac{1}{I_{IND(ripple)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}} = \frac{3}{I_{OUT(max)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}}$$
(8)

The inductor requires a low DCR to achieve good efficiency. It also requires enough room above peak inductor current before saturation. The peak inductor current can be estimated in Equation 9.

$$I_{\text{IND(peak)}} = \frac{V_{\text{TRIP}}}{32 \times R_{\text{DS(on)}}} + \frac{1}{L \times f_{\text{SW}}} \times \frac{\left(V_{\text{IN}(\text{max})} - V_{\text{OUT}}\right) \times V_{\text{OUT}}}{V_{\text{IN}(\text{max})}}$$
(9)

(11)

STRUMENTS

4. External component selection with all ceramic output capacitors

Refer to *External Component Selection Using All Ceramic Output Capacitors* to select external components because ceramic output capacitors are used in this design.

5. Choose the overcurrent setting resistor

The overcurrent setting resistor, R_{TRIP} , can be determined by Equation 10.

$$R_{TRIP}(k\Omega) = \frac{\left(I_{OCP} - \left(\frac{1}{2 \times L \times f_{SW}}\right) \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}}\right) \times 32 \times R_{DS(on)}(m\Omega)}{I_{TRIP}(\mu A)}$$

where

- I_{TRIP} is the TRIP pin sourcing current (10 μA)
- R_{DS(on)} is the thermally compensated on-time resistance value of the low-side MOSFET (10)

Use an $R_{DS(on)}$ value of 1.5 m Ω for an overcurrent level of approximately 30 A. Use an $R_{DS(on)}$ value of 1.7 m Ω for overcurrent level of approximately 10 A.

8.2.1.2.2 External Component Selection Using All Ceramic Output Capacitors

When a ceramic output capacitor is used, the stability criteria in Equation 7 cannot be satisfied. The ripple injection approach as shown in Figure 38 is implemented to increase the ripple on the VFB pin and make the system stable. In addition to the selections made using steps 1 through step 6 in *External Component Selection*, the ripple injection components must be selected. The C2 value can be fixed at 1 nF. The value of C1 can be selected between 10 nF to 200 nF.

$$\frac{L \times C_{OUT}}{R7 \times C1} > N \times \frac{t_{ON}}{2}$$

where

N is the coefficient to account for L and C_{OUT} variation

N is also used to provide enough margin for stability. It is recommended N=2 for $V_{OUT} \le 1.8$ V and N=4 for $V_{OUT} \ge 3.3$ V or when L ≤ 250 nH. The higher V_{OUT} needs a higher N value because the effective output capacitance is reduced significantly with higher DC bias. For example, a 6.3-V, 22-µF ceramic capacitor may have only 8 µF of effective capacitance when biased at 5 V.

Because the VFB pin voltage is regulated at the valley, the increased ripple on the VFB pin causes the increase of the VFB DC value. The AC ripple coupled to the VFB pin has two components, one coupled from SW node and the other coupled from the VOUT pin and they can be calculated using Equation 12 and Equation 13 when neglecting the output voltage ripple caused by equivalent series inductance (ESL).

$$V_{INJ_SW} = \frac{V_{IN} - V_{OUT}}{R7 \times C1} \times \frac{D}{f_{SW}}$$
(12)

$$V_{INJ_OUT} = ESR \times I_{IND(ripple)} + \frac{I_{IND(ripple)}}{8 \times C_{OUT} \times f_{SW}}$$
(13)

It is recommended that V_{INJ_SW} to be less than 50 mV. If the calculated V_{INJ_SW} is higher than 50 mV, then other parameters need to be adjusted to reduce it. For example, C_{OUT} can be increased to satisfy Equation 11 with a higher R7 value, thereby reducing V_{INJ_SW} .

The DC voltage at the VFB pin can be calculated by Equation 14:

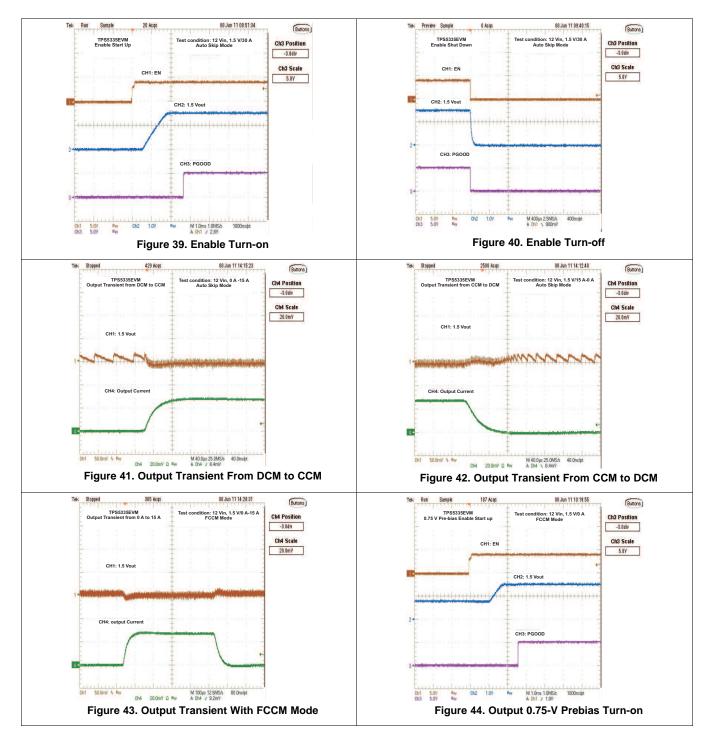
$$V_{VFB} = 0.6 + \frac{V_{INJ}SW + V_{INJ}OUT}{2}$$
(14)

And the resistor divider value can be determined by Equation 15:

$$R1 = \frac{V_{OUT} - V_{VFB}}{V_{VFB}} \times R2$$
(15)



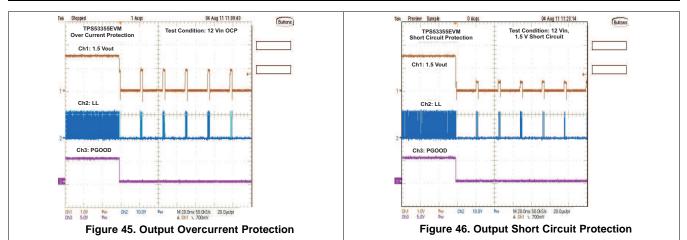
8.2.1.3 Application Curves





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8.2.2 Typical Application Circuit

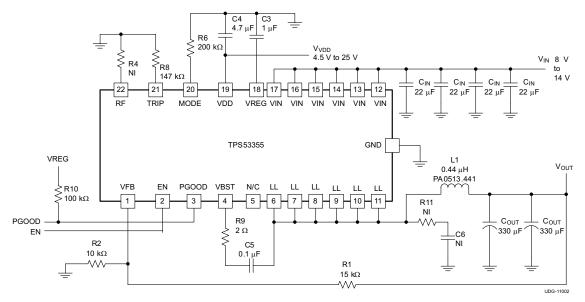


Figure 47. Typical Application Circuit Diagram

8.2.2.1 Design Requirements

Table 5. Design Parameters

	PARAMETER	TEST CONDITION	MIN	ТҮР	MAX	UNIT
INPUT CH	HARACTERISTICS					
V _{IN}	Voltage range		8	12	14	V
	Maximum input current	V _{IN} = 8 V, I _{OUT} = 30 A		6.3		А
I _{MAX}	No load input current	$V_{IN} = 14 \text{ V}, I_{OUT} = 0 \text{ A with auto-skip}$ mode		1		mA
OUTPUT	CHARACTERISTICS					
	Output voltage			1.5		
V _{OUT}		Line regulation, 8 V \leq V _{IN} \leq 15 V		0.1%		
•001	Output voltage regulation	Load regulation, $V_{IN} = 12 \text{ V}, 0 \text{ A} \le I_{OUT} \le 30 \text{ A}$ with FCCM		0.2%		
V _{RIPPLE}	Output voltage ripple	$V_{IN} = 12 \text{ V}, I_{OUT} = 30 \text{ A with FCCM}$		20		mV _{PP}
I _{LOAD}	Output load current		0		30	А
I _{OCP}	Output overcurrent threshold			34		А

Table 5. Design Parameters (continued)

	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
t _{SS}	Soft-start time			1.4		ms
SYSTEM	S CHARACTERISTICS					
f _{SW}	Switching frequency			500		kHz
	Peak efficiency	$V_{IN} = 12 \text{ V}, V_{OUT} = 1.1 \text{ V}, I_{OUT} = 10 \text{ A}$		91.87%		
η	Full load efficiency	$V_{IN} = 12 \text{ V}, V_{OUT} = 1.1 \text{ V}, I_{OUT} = 30 \text{ A}$		89.46%		
T _A	Operating temperature			25		°C

8.2.2.2 Detailed Design Procedure

8.2.2.2.1 External Component Selection

Refer to *External Component Selection Using All Ceramic Output Capacitors* for guidelines for this design with all ceramic output capacitors.

The external components selection is a simple process when using organic semiconductors or special polymer output capacitors.

1. Select operation mode and soft-start time

Select operation mode and soft-start time using Table 3.

2. Select switching frequency

Select the switching frequency from 250 kHz to 1 MHz using Table 1.

3. Choose the inductor

The inductance value should be determined to give the ripple current of approximately 1/4 to 1/2 of maximum output current. Larger ripple current increases output ripple voltage and improves signal-to-noise ratio and helps ensure stable operation, but increases inductor core loss. Using 1/3 ripple current to maximum output current ratio, the inductance can be determined by Equation 16.

$$L = \frac{1}{I_{IND(ripple)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}} = \frac{3}{I_{OUT(max)} \times f_{SW}} \times \frac{\left(V_{IN(max)} - V_{OUT}\right) \times V_{OUT}}{V_{IN(max)}}$$
(16)

The inductor requires a low DCR to achieve good efficiency. It also requires enough room above peak inductor current before saturation. The peak inductor current can be estimated in Equation 9.

$$I_{\text{IND}(\text{peak})} = \frac{V_{\text{TRIP}}}{32 \times R_{\text{DS}(\text{on})}} + \frac{1}{L \times f_{\text{SW}}} \times \frac{\left(V_{\text{IN}(\text{max})} - V_{\text{OUT}}\right) \times V_{\text{OUT}}}{V_{\text{IN}(\text{max})}}$$
(17)

4. Choose the output capacitors

When organic semiconductor capacitor(s) or specialty polymer capacitor(s) are used, for loop stability, capacitance and ESR should satisfy Equation 7. For jitter performance, Equation 18 is a good starting point to determine ESR.

$$\mathsf{ESR} = \frac{\mathsf{V}_{\mathsf{OUT}} \times 10\,\mathsf{mV} \times (1-\mathsf{D})}{0.6\,\mathsf{V} \times \mathsf{I}_{\mathsf{IND}(\mathsf{ripple})}} = \frac{10\,\mathsf{mV} \times \mathsf{L} \times \mathsf{f}_{\mathsf{SW}}}{0.6\,\mathsf{V}} = \frac{\mathsf{L} \times \mathsf{f}_{\mathsf{SW}}}{60} \left(\Omega\right)$$

where

- D is the duty factor.
- The required output ripple slope is approximately 10 mV per t_{SW} (switching period) in terms of VFB terminal voltage. (18)

5. Determine the value of R1 and R2

The output voltage is programmed by the voltage-divider resistor, R1 and R2 shown in Figure 37. R1 is connected between VFB pin and the output, and R2 is connected between the VFB pin and GND. Recommended R2 value is from 1 k Ω to 20 k Ω . Determine R1 using Equation 19.

$$R1 = \frac{V_{OUT} - \frac{I_{IND(ripple}) \times ESR}{2} - 0.6}{0.6} \times R2$$

(19)

(20)

6. Choose the overcurrent setting resistor

The overcurrent setting resistor, R_{TRIP} , can be determined by Equation 10.

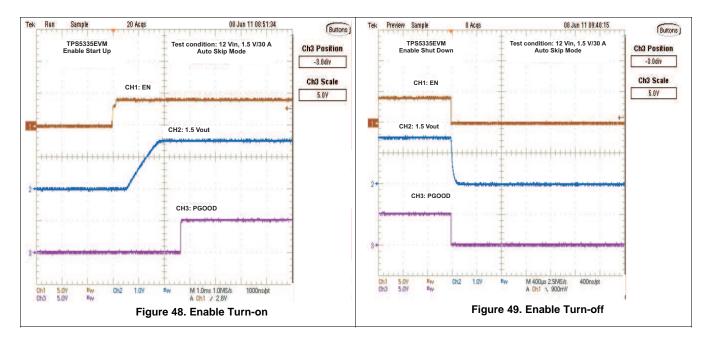
$$R_{TRIP}(k\Omega) = \frac{\left(I_{OCP} - \left(\frac{1}{2 \times L \times f_{SW}}\right) \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}}\right) \times 32 \times R_{DS(on)}(m\Omega)}{I_{TRIP}(\mu A)}$$

where

- I_{TRIP} is the TRIP pin sourcing current (10 μ A)
- R_{DS(on)} is the thermally compensated on-time resistance value of the low-side MOSFET

Use an $R_{DS(on)}$ value of 1.5 m Ω for an overcurrent level of approximately 30 A. Use an $R_{DS(on)}$ value of 1.7 m Ω for overcurrent level of approximately 10 A.

8.2.2.3 Application Curves





9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range between 1.5 V and 22 V (4.5-V to 25-V biased). This input supply must be well regulated. Proper bypassing of input supplies and internal regulators is also critical for noise performance, as is PCB layout and grounding scheme. See the recommendations in *Layout*.

10 Layout

10.1 Layout Guidelines

Certain points must be considered before starting a layout work using the TPS53355.

- The power components (including input/output capacitors, inductor and TPS53355) should be placed on one side of the PCB (solder side). At least one inner plane should be inserted, connected to ground, in order to shield and isolate the small signal traces from noisy power lines.
- All sensitive analog traces and components such as VFB, PGOOD, TRIP, MODE and RF should be placed away from high-voltage switching nodes such as LL, VBST to avoid coupling. Use internal layer(s) as ground plane(s) and shield feedback trace from power traces and components.
- Place the VIN decoupling capacitors as close to the VIN and PGND pins as possible to minimize the input AC current loop.
- Because the TPS53355 controls output voltage referring to voltage across VOUT capacitor, the top-side
 resistor of the voltage divider should be connected to the positive node of the VOUT capacitor. The GND of
 the bottom side resistor should be connected to the GND pad of the device. The trace from these resistors to
 the VFB pin should be short and thin.
- Place the frequency setting resistor (R_F), OCP setting resistor (R_{TRIP}) and mode setting resistor (R_{MODE}) as close to the device as possible. Use the common GND via to connect them to GND plane if applicable.
- Place the VDD and VREG decoupling capacitors as close to the device as possible. Make sure GND vias are provided for each decoupling capacitor and make the loop as small as possible.
- The PCB trace defined as switch node, which connects the LL pins and high-voltage side of the inductor, should be as short and wide as possible.
- Connect the ripple injection V_{OUT} signal (V_{OUT} side of the C1 capacitor in Figure 38) from the terminal of ceramic output capacitor. The AC coupling capacitor (C2 in Figure 38) should be placed near the device, and R7 and C1 can be placed near the power stage.
- Use separate vias or trace to connect LL node to snubber, boot strap capacitor and ripple injection resistor. Do not combine these connections.

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10.2 Layout Example

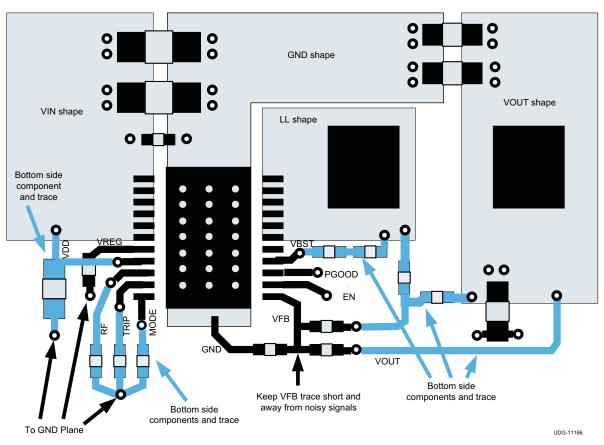


Figure 50. Layout Recommendation



11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Community Resources

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11.3 Trademarks

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11.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



15-Apr-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
HPA01111DQPR	ACTIVE	LSON-CLIP	DQP	22	2500	Pb-Free (RoHS Exempt)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	53355DQP	Samples
TPS53355DQPR	ACTIVE	LSON-CLIP	DQP	22	2500	Pb-Free (RoHS Exempt)	CU NIPDAU CU SN	Level-2-260C-1 YEAR	-40 to 85	53355DQP	Samples
TPS53355DQPT	ACTIVE	LSON-CLIP	DQP	22	250	Pb-Free (RoHS Exempt)	CU NIPDAU CU SN	Level-2-260C-1 YEAR	-40 to 85	53355DQP	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

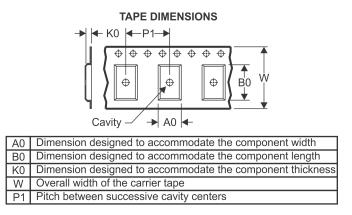
www.ti.com

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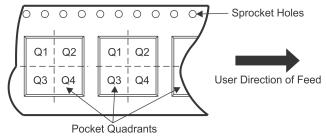
TAPE AND REEL INFORMATION



*All dimensions are nominal



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS53355DQPR	LSON- CLIP	DQP	22	2500	330.0	15.4	5.3	6.3	1.8	8.0	12.0	Q1
TPS53355DQPT	LSON- CLIP	DQP	22	250	330.0	15.4	5.3	6.3	1.8	8.0	12.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

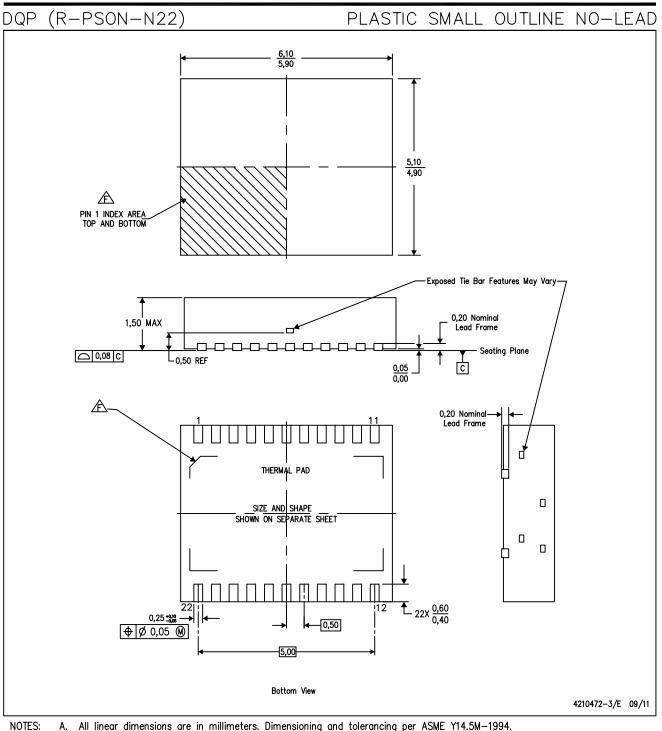
6-Jun-2018



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS53355DQPR	LSON-CLIP	DQP	22	2500	336.6	336.6	41.3
TPS53355DQPT	LSON-CLIP	DQP	22	250	336.6	336.6	41.3

MECHANICAL DATA



All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. Α.

- B. This drawing is subject to change without notice.
- Small Outline No-Lead (SON) package configuration. C.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- 🖄 Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated.
 - The Pin 1 identifiers are either a molded, marked, or metal feature.



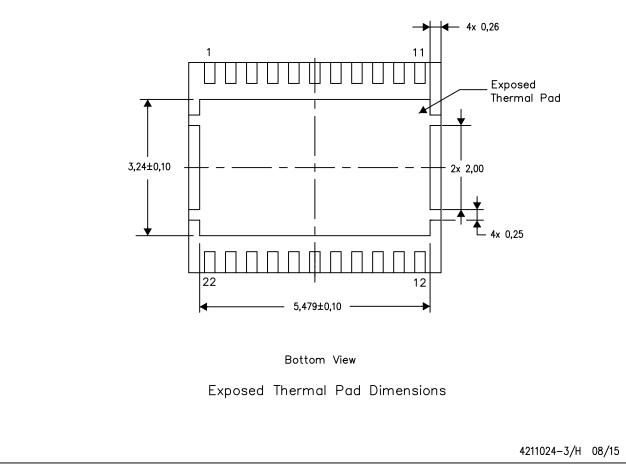
DQP (R-PSON-N22) PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

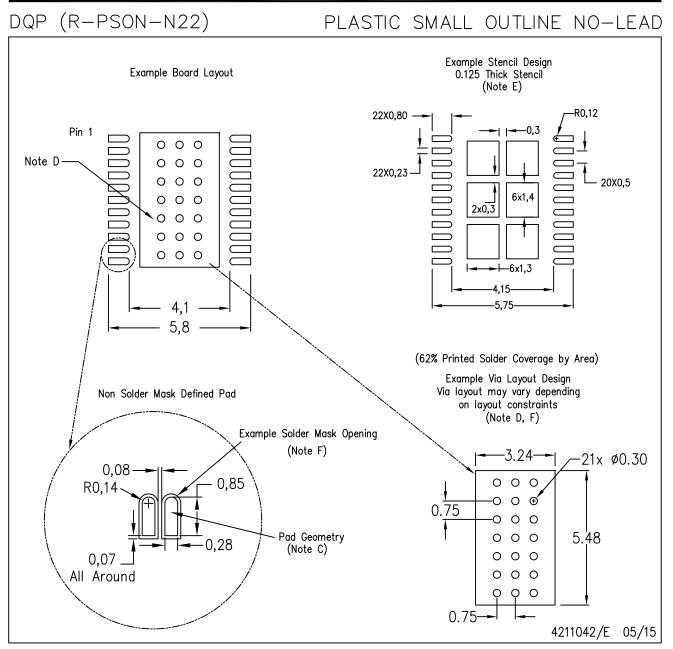
For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters





NOTES: A.

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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